In the Claims

The following Listing of Claims replaces all prior versions in the application:

LISTING OF CLAIMS

1. (Previously presented) A method for manufacturing at least one electrode on a II-VI semiconducting material or a compound of the II-VI semiconductor material, the at least one electrode being in a metal for which the work function is substantially equal to or larger than that of the II-VI semiconducting material, this method being characterized in that the at least one electrode is formed by electrochemical deposition of the metal from a solution of a metal chloride ~~of the metal~~ in pure hydrochloric acid, the metal chloride being a chloride of said metal, and wherein pure hydrochloric acid is the liquid which is obtained by dissolving about 37% to about 38% by weight of hydrogen chloride gas molecules in water.

2. (Previously presented) The method according to claim 1, wherein the metal is gold or platinum and a gold chloride solution or a platinum chloride solution in pure hydrochloric acid is used.

3. (Previously presented) The method according to claim 2, wherein a concentration of gold chloride or platinum chloride in pure hydrochloric acid is less than 5%.

4. (Currently Amended) The method according to claim 1, wherein a surface of the II-VI semiconducting material or of the compound of the II-WI semiconductor material is prepared before the deposition in order to make this surface capable of fixing the metal.

5. (Currently Amended) The method according to claim 4, wherein the surface of the II-VI semiconducting material or of the compound of the II-WI semiconductor material is chemically etched in a solution comprising hydrochloric acid.

6. (Previously presented) The method according to claim 5, wherein the metal is gold or platinum, a gold or platinum chloride solution in pure hydrochloric acid is used and a solution of bromine and hydrochloric acid is used for the chemical etching.

7. (Previously presented) The method according to claim 1, wherein the II-VI semiconducting material is CdTe.

8. (Previously presented) The method according to claim 7, wherein the at least one electrode is formed on a compound of CdTe which is selected from CdZnTe, CdTe:Cl, CdTeSe:Cl, CdZnTe:Cl, CdTe:In, CdZnTe:In and CdHgTe.

9. (Previously presented) The method according to claim 6, wherein a solution of bromine and pure hydrochloric acid is used for the chemical etching.

10. (Canceled)

11. (Currently amended) The method according to claim 1, wherein a concentration of the metal chloride ~~of the metal~~ in pure hydrochloric acid is less than 5%.

12. (Currently amended) The method according to claim 5, wherein the II-VI semiconducting material or the compound of the II-VI semiconducting material is rinsed in pure hydrochloric acid after chemically etching the surface of the II-VI semiconducting material or of the compound of the II-VI semiconducting material.

13. (Currently amended) The method according to claim 1, wherein a rinse of the II-VI semiconducting material or the compound of the II-VI semiconducting material is performed in hydrochloric acid and then in water, after electrochemical deposition of the metal is completed.

14. (New) The method according to claim 1, wherein the electrode comprises a layer of the metal having a thickness of about 100 nm to about 150 nm.

15. (New) The method according to claim 14, wherein the electrode comprises a layer of the metal capable of withstanding a peeling force larger than about 10 kg/cm^2.